First-principles investigation of paramagnetic centers in P₂O₅ based glasses

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Abstract—We present a first-principles investigation of paramagnetic centers in P_2O_5 based on the calculation of electron paramagnetic resonance (EPR) parameters (g-tensor and Fermi contacts). Calculations of the EPR parameters for the P_1 configuration in crystalline o'(P_2O_5) support the previous attribution of the P_1 to a P-defect structurally analogous to the Si-E' center. As far as concerns the P_1 center in glassy P_2O_5 , the present work suggests the possible occurrence of another configuration besides the analogue of the Si-E' center. Such an alternative P_1 center configuration is likely to be relevant for those P_2O_5 based glasses featuring a considerable fraction of Q_1 and Q_2 tetrahedral units besides the Q_3 unit which dominates the structure of pure P_2O_5 .

Keywords—P2O5, P1 center, Si-E' center, first-principles

I. INTRODUCTION

Phosphate glasses, due to their low Tg (~300 to 500 °C) and melting temperature (~800 to 1300 °C) facilitating the final formation process, are used in various industrial applications. In nuclear waste storage, in particular by means of vitrification processes, iron-phosphate glasses are regarded as a stable storage medium for high-level nuclear waste. In microelectronics, phosphosilicate glass (PSG) is employed to stabilize the field effect transistor (FET) device, since the PSG traps impurity ions, namely Na⁺, which would be detrimental for the correct functioning of the device [1]. Furthermore the PSG is used for photovoltaic applications as a dopant source in the fabrication of crystalline silicon solar cells [2]. For optical applications, phosphate glasses are widely used, in particular, doped with rare-earth elements. For instance, phosphate glasses doped with Yb give highly efficient emission at ~1000 nm. As the dissolution of rare-earth ions is much more easier in a phosphate matrix than in silicate glasses, phosphate glasses can be used as laser glass for the production of high-power solid-state lasers systems [3]. Similarly, in silica glass, it has been shown that P-codoping is more efficient to dissolve a rare-earth element such as Yb, than Al-codoping. In fact the P-codoping allows to avoid the Yb cluster formation, which limits the efficiency of Yb³⁺ emission [4].

Ionizing irradiation induces many point defects in phosphate and phospho-silicate glasses [5,6,7]. Several

paramagnetic point defects have been detected: the so-called P_1 , P_2 , P_3 , P_4 and r-POHC, and l-POHC centers. The radiation induced generation of the latter phosphorus oxygen hole centers (POHC) has an almost linear dependence on the dose, so that phosphate glasses are nowadays considered also for dosimetry applications [7]. The P_1 center gives rise to an absorption band peaking at about 0.79 eV, which is detrimental for transmission in the infrared domain [6].

Although the P_1 center is commonly accepted to be analogous to the Si-*E*' center [6,8,9], its experimental characterization in phosphate glasses, and in particular in pure P_2O_5 glass, is rather poor (as compared to Si-*E*') and mainly based on a 30 years old data analysis [5,6]. The present work aims, mainly by means of theoretical first-principles techniques for the calculation of electron paramagnetic resonance (EPR) parameters, to improve our understanding and modelling of point defects, namely of the P_1 center, in P_2O_5 containing glasses.

II. METHODS & MODELS

The calculations presented in this work are based on density functional theory (DFT). The codes we used are freely available with the Quantum-Espresso (QE) package [10]. We used the QE-GIPAW code that exploits the gauge including projector augmented wave (GIPAW) method for the calculation of the EPR parameters [10,11] The Perdew-Burke-Ernzerhof exchange correlation functional (PBE) has been adopted for the present calculations [12]. Norm-conserving Trouiller-Martins gipaw pseudopotentials are used and Kohn-Sham wavefunctions are expanded in a basis of plane waves up to a kinetic cutoff of 70 Ry. The defect configurations here analyzed have been obtained by using a o'(P2O5) crystal model and a recently generated vitreous P₂O₅ model both consisting of a 112 atoms supercell with 32 regular corner-sharing PO₄ tetrahedral units. Regular PO₄ units exhibit three normal P-O bonds and one P=O double bond, and are sometimes labelled as Q₃ units [13]. Configurations of paramagnetic centers (POHC, P1 P2) are obtained by removing a terminal oxygen from one PO₄ tetrahedron and then by performing a firstprinciples relaxation of the atomic structure which is put in a positive charge state. Next EPR parameters (*g*-tensors and Fermi-contacts) are calculated by using the QE-GIPAW code. The calculations of the computationally expensive *g*-tensor have been carried out only for a selected number of configurations.

III. RESULTS

A. g-tensor and Fermi-contact analysis of selected paramagnetic configurations in P₂O₅

Despite we are not aware of any EPR measurements on irradiated crystalline o'(P₂O₅) we still begin our investigation by considering oxygen vacancies, at terminal oxygen atoms, in $o'(P_2O_5)$ where there is no issue concerning the structural arrangement of atoms. The spin density of our P₁ defect configuration in $O'(P_2O_5)$ is shown in Fig. 1: the spin-density mainly localizes on a sp^3 dangling bond at the three-fold P atom, similarly to a Si-E' center. However, terminal oxygen atoms of nearby [(O-)₃P=O] tetrahedra also show some spindensity localization. For the three-fold P atom shown in Fig. 1, the average O-P-O bond angle is 106.3° and P-O bond length is 1.57 Å. The calculated g-principal values and Fermi contacts are $g_1 = 2.0023$, $g_2 = 2.0038$, $g_3 = 2.0063$, and $A_{iso}(^{31}P)$ = 105.8 mT. Such values are in a reasonable agreement with the available experimental data [5]: $\langle g \rangle = 2.005$, A_{iso}(³¹P) = 95 mT, and provide a solid ground for further investigations in P₂O₅ based glasses. Note that although only the average value $\langle g \rangle$ was given in [5] a certain anisotropy could be expected on the basis of the experimental EPR parameters of the P_1 center in P-doped silica: $g_{\parallel}=2.002$, $g_{\perp}=1.999$, and A_{iso} (³¹P)=91 mT [6]. As previously shown by Abarenkov et al [14], the top of the valence band of P_2O_5 mainly comprises of O 2p states which, given the large number of terminal oxygen atoms. implies an ease of formation of phosphorus-oxygen hole centers (POHC). In fact, by applying the same procedure used to generate a P_1 center in the o'(P_2O_5) crystal (i.e. removing one terminal oxygen atom and one electron and subsequently carrying out an *ab-initio* relaxation of the atomic structure, see also the following discussion on the Fermi contacts distribution) we have generated P1, P2 and also POHC-like center (Fig. 2) in our glass model of P₂O₅. The g principal values calculated for the configuration shown in Fig. ¹ 2 are $g_1 = 2.013$, $g_2 = 2.018$, $g_3 = 2.019$, which indeed speak for a center resembling a POHC [6]. Note that this configuration features a (neutral) three coordinated P atom with average P-O bond length of 1.67 Å and O-P-O angle of 96.7°. Only a few terminal oxygen sites in the glass allowed for the generation of a P₁ center configuration similar to the one discussed here above in the crystalline o'(P₂O₅) model structure. Moreover, from a direct inspection of the spin-density, only one configuration shows a spin-density very close to the ideal sp^3 typical of E' centers, whereas the others all shows spin-density localization on a fourth nearby oxygen atom, thus reminiscing of the spin-density of a P₂ center. The calculated g-principal values and Fermi contacts of our "ideal" P1 configuration are $g_1 = 2.0018$, $g_2 = 2.0026$, $g_3 = 2.0036$, and Aiso(P) = 98.5 mT. The formation energy [9] calculated for the neutral oxygen vacancy at this site is about 2.7 eV (for a few other oxygen vacancy sites we found formation energies to be in the range 2.3 to 2.8 eV), about 2 eV less than reported for neutral oxygen vacancies in silica [9]. In the neutral charge state, the average P-O bond length is 1.67 Å, and O-P-O angle is 97.7°, while once it is positively charged the P-O bond length becomes 1.57 Å and O-P-O 108.8°.



Fig. 1: Spin-density (shaded) of a P_1 configuration (positively charged oxygen vacancy obtained from removal of a terminal oxygen) in o'(P_2O_5).

In the glass, we also generated a considerable number of P₂ center configurations. The calculated *g*-principal values and Fermi contacts of a typical P₂ configuration are $g_1 = 2.0002$, $g_2 = 2.0027$, $g_3 = 2.0038$, and $A_{iso}({}^{31}P) = 142.5$ mT which is in reasonable agreement with [5]. The PO₄ tetrahedron of this P₂ configuration is remarkably distorted, as previously found for P₂ centers in P-doped silica [15], and shows a wide O-P-O angle of 163.6° between two long P-O bonds (1.69 and 1.95 Å), while the other two P-O bonds are shorter (1.61 Å) and form a O-P-O angle of 101.1°.

An alternative model for the P_1 center, not structurally analogous to the Si-*E*' center, was obtained by adding a PO₂ unit nearby a terminal oxygen atom and then by carrying out a first principles relaxation of the structure. The spin-density of the final configuration is shown in Fig. 3.



Fig. 2: POHC-like spin-density (shaded) of the positively charged P_2O_5 glass model containing an oxygen vacancy obtained from removal of a terminal oxygen atom.





Fig. 3: Spin-density (shaded) of the P_1 -like configuration obtained after placing an extra PO₂ unit nearby a terminal oxygen in a P_2O_5 glass model.

The P atom bearing the unpaired spin in Fig. 3 forms one double bond with a terminal oxygen (1.49 Å) and two bonds with bridging oxygen atoms (1.87 Å and 1.55 Å). The spin-density shown in Fig. 3 is very similar to the one shown in Fig. 1, thus suggesting its classification as a P₁ center configuration. Moreover, the Fermi contact A_{iso} (³¹P)=101.3 mT and the *g* principal values g_1 =1.9969, g_2 =2.0023, g_3 =2.0049 calculated for the configuration shown in Fig. 3 further support its attribution to a paramagnetic defect of the P₁ center type [6]. In the table Tab. 1, we summarize the results of our EPR calculations for the three P₁-like configurations generated in the present work, according to the number of non-bridging oxygen (NBO) atoms.

B. Fermi contacts A_{iso}(³¹P) distribution of oxygen vacancies in P₂O₅ glass

The Weeks & Bray paper [5] is to our knowledge, the only paper which addresses the irradiation induced generation of paramagnetic centers in pure P₂O₅. However, also because the information on g-tensors given in [5] is rather scarce, we have dedicated more attention to the hyperfine splittings and in particular we have obtained the distribution of Fermi contacts Aiso(³¹P) calculated for all the paramagnetic configurations generated at a terminal oxygen site in our model of vitreous P₂O₅. In agreement with Weeks & Bray [5], the present investigation shows (Fig. 4) that in pure P_2O_5 the presence of oxygen vacancies (at the terminal oxygen) leads to the three kinds of EPR centers mentioned here above (P1, P2, POHC), so that the occasional presence of centers other than the three under discussion should be ascribed to the occurence of impurities in P2O5 [5]. Among the three kinds of centers which are emphasized in Fig. 4 with circles, the lowest

Number of NBO	structure	g_1	g ₂	g 3	Aiso(P)
0	0'(P2O5)	2.0023	2.0038	2.0063	105.8
0	glass	2.0018	2.0026	2.0036	98.5
1	glass	1.9969	2.0023	2.0049	101.3

Fig. 5: Fermi-contacts $A_{iso}({}^{31}P)$ distribution of oxygen vacancies (at a nonbridging oxygen atom) in a P₂O₅ glass model.

(relative) energy one corresponds to P₂ centers which exhibit Fermi contacts in the range ~130-150 mT. P₁ centers and POHC centers have a larger relative energy 0.6-1.0 eV. However these differences, when considering a nonequilibrium condition (irradiation) are rather small and do not imply necessarily a preference for the generation of P₂ centers. Moreover, we here only generated a few P₁-like configurations so that, with a more statistically significative set of configurations, their average relative energy difference with respect to P₂ could become smaller.

IV. CONCLUSIONS

We performed first-principles calculations of the structure and of the EPR parameters for the P1, P2 and POHC paramagnetic centers in o'(P2O5) and P2O5 glass. The results are satisfactory and confirm the validity of the adopted theoretical approach to model paramagnetic defects in phosphate glasses and support for the P_1 a structural analogy to the Si-E' center. It should be noted however that only a minor fraction (~15%) of the oxygen vacancy sites in the glass here considered allow for the generation of a P1-like configuration. In fact, the vast majority of the terminal oxygen vacancy sites allows for the generation of POHC and P2 centers in a similar amount. As far as concerns the P1 center in glassy P₂O₅, the present work suggests the possible occurrence of another configuration besides the previous one, i.e. a three-fold P atom featuring a P=O double bond and two normal P-O bonds. Such an alternative P1 center configuration is likely to be relevant for those glasses featuring a considerable fraction of Q1, Q2 tetrahedral units besides the Q3 unit which dominates the structure of pure P_2O_5 glass [13].

ACKNOWLEDGMENT

We acknowledge support through the ARRS-CEA Bilateral Project "REPHLES" NC-0008.

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